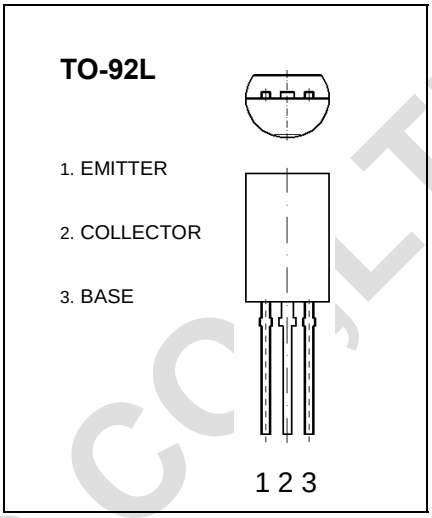
KSC2330 TRANSISTOR (NPN)



FEATURE

Power dissipation

$P_{CM:}$ 1 W (Tamb=25℃)

Collector current

$I_{CM:}$ 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= 100μA, I_E=0	300		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 5mA, IB=0	300		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	7		V
Collector cut-off current	I_{CBO}	V_{CB}=200V, IE=0		0.1	μA
DC current gain	h_{FE}	V_{CE}=10 V, IC= 20mA	40	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= 10m A, I_B= 1mA		0.5	V
Transition frequency	f_T	V_{CE}= 30 V, I_C= 10mA	50		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	120-240